

IN THE SPECIFICATION:

Please replace the paragraph at page 1, lines 4-5 with the following rewritten paragraph:

This is a Continuation of Application No. 09/895,205 filed July 2, 2001, which in turn claims priority under 35 U.S.C. §119 of Japanese Patent Application No. 2000-206588, filed July 7, 2000. The entire disclosure of the prior application, together with the foreign priority application, is hereby incorporated by reference in its entirety.

Please replace the paragraph at page 5 lines 2-11 with the following rewritten paragraph:

(4) the memory cell array may comprise an insulating substrate on which is formed the first signal electrodes, the ferroelectric layers, and the second signal electrodes, the ferroelectric layer may be formed in a divided manner and disposed in the intersection regions between the first signal electrodes and the second signal electrodes, and dielectric layers differing from the ferroelectric layers may be formed between the adjacent divided ferroelectric layers. The dielectric layers may be formed of a material with a dielectric constant smaller than a dielectric constant of the ferroelectric layer.